

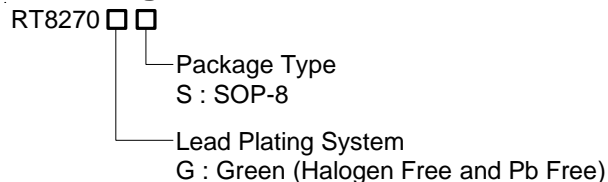
2A, 22V, 1.2MHz Step-Down Converter

General Description

The RT8270 is an asynchronous high voltage buck converter that can support the input voltage range from 4.75V to 22V and the output current can be up to 2A. Current Mode operation provides fast transient response and eases loop stabilization.

The chip provides protection functions such as cycle-by-cycle current limiting and thermal shutdown protection. In shutdown mode, the regulator draws 25µA of supply current. The RT8270 is available in a SOP-8 surface mount package.

Ordering Information



Note :

Richtek products are :

- ▶ RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- ▶ Suitable for use in SnPb or Pb-free soldering processes.

Marking Information

For marking information, contact our sales representative directly or through a Richtek distributor located in your area, otherwise visit our website for detail.

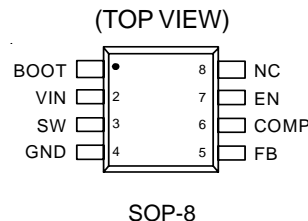
Features

- Wide Operating Input Range : 4.75V to 22V
- Adjustable Output Voltage Range : 1.222V to 16V
- Output Current up to 2A
- 25µA Low Shutdown Current
- Power MOSFET : 0.18Ω
- High Efficiency up to 95%
- 1.2MHz Fixed Switching Frequency
- Stable with Low ESR Output Ceramic Capacitors
- Thermal Shutdown Protection
- Cycle-By-Cycle Over Current Protection
- RoHS Compliant and Halogen Free

Applications

- Distributive Power Systems
- Battery Charger
- DSL Modems
- Pre-regulator for Linear Regulators

Pin Configurations



Typical Application Circuit

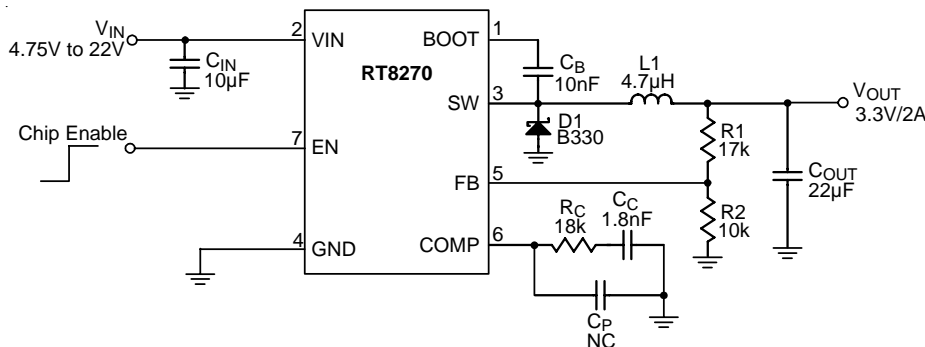


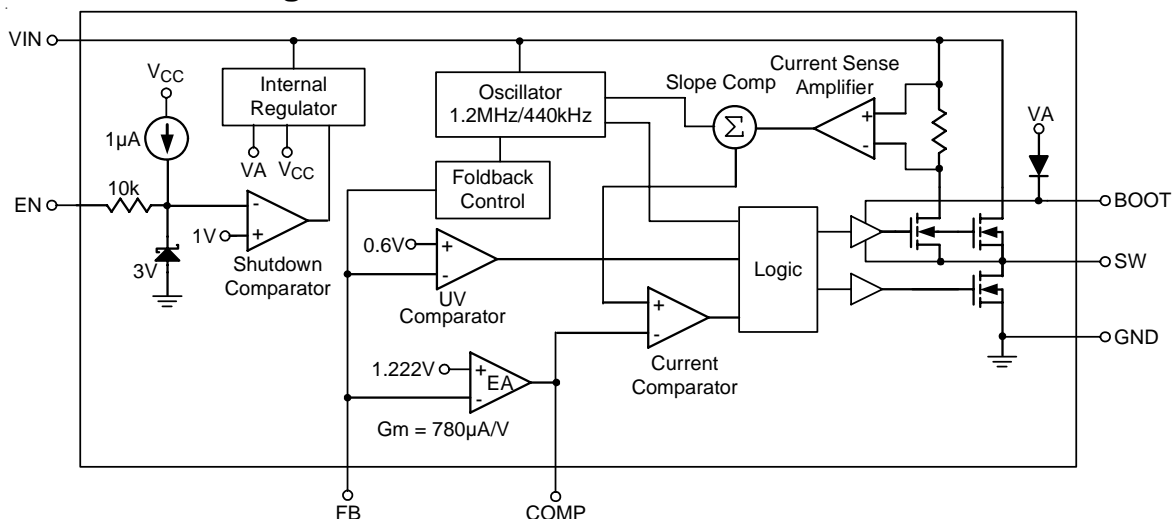
Table 1. Recommended Component Selection

V _{OUT} (V)	R1 (kΩ)	R2 (kΩ)	R _C (kΩ)	C _C (nF)	L1 (μH)	C _{OUT} (μF)
12	88.7	10	51	0.86	10	22
5	30	10	23.1	1.2	6.8	22
3.3	17	10	18	1.8	4.7	22
2.5	10.45	10	12	2.2	4.7	22
1.8	4.75	10	10	2.2	2.2	22
1.222	0	10	9.1	2.2	2.2	22

Functional Pin Description

Pin No.	Pin Name	Pin Function
1	BOOT	High Side Gate Drive Boost Input. BOOT supplies the drive for the high side N-MOSFET switch. Connect a 10nF or greater capacitor from SW to BOOT to power the high side switch.
2	VIN	Power Input. V _{IN} supplies the power to the IC, as well as the step-down converter switches. Bypass VIN to GND with a suitable large capacitor to eliminate noise on the input to the IC.
3	SW	Power Switching Output. SW is the switching node that supplies power to the output. Connect the output LC filter from SW to the output load. Note that a capacitor is required from SW to BOOT to power the high side switch.
4	GND	Ground.
5	FB	Feedback Input. FB senses the output voltage to regulate said voltage. The feedback reference voltage is 1.222V typically.
6	COMP	Compensation Node. COMP is used to compensate the regulation control loop. Connect a series RC network from COMP to GND to compensate the regulation control loop. In some cases, an additional capacitor from COMP to GND is required.
7	EN	Enable Input. EN is a digital input that turns the regulator on or off. Drive EN higher than 1.4V to turn on the regulator, lower than 0.4V to turn it off. If the EN pin is open, it will be pulled to high by internal circuit.
8	NC	No Internal Connection.

Function Block Diagram



Absolute Maximum Ratings (Note 1)

- Supply Voltage, V_{IN} ----- 23V
- Switching Voltage, SW ----- -0.3V to ($V_{IN} + 0.3V$)
- BOOT Voltage ----- ($V_{SW} - 0.3V$) to ($V_{SW} + 6V$)
- All Other Voltage ----- -0.3V to 6V
- Power Dissipation, P_D @ $T_A = 25^\circ C$
 SOP-8 ----- 0.833W
- Package Thermal Resistance (Note 2)
 SOP-8, θ_{JA} ----- 120°C/W
- Junction Temperature ----- 150°C
- Lead Temperature (Soldering, 10 sec.) ----- 260°C
- Storage Temperature Range ----- -65°C to 150°C
- ESD Susceptibility (Note 3)
 HBM (Human Body Mode) ----- 2kV
 MM (Machine Mode) ----- 200V

Recommended Operating Conditions (Note 4)

- Supply Voltage, V_{IN} ----- 4.75V to 22V
- Enable Voltage, V_{EN} ----- 0V to 5.5V
- Junction Temperature Range ----- -40°C to 125°C
- Ambient Temperature Range ----- -40°C to 85°C

Electrical Characteristics

($V_{IN} = 12V$, $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Feedback Reference Voltage	V_{FB}	$4.75V \leq V_{IN} \leq 22V$	1.184	1.222	1.258	V
High Side Switch-On Resistance	$R_{DS(ON)1}$		--	0.18	--	Ω
Low Side Switch-On Resistance	$R_{DS(ON)2}$		--	10	--	Ω
Switch Leakage		$V_{EN} = 0V$, $V_{SW} = 0V$	--	--	10	μA
Current Limit	I_{LIM}	Duty = 90%; $V_{BOOT-SW} = 4.8V$	--	3	--	A
Current Sense Transconductance	G_{CS}	Output Current to V_{COMP}	--	2.5	--	A/V
Error Amplifier Transconductance	G_m	$\Delta I_C = \pm 10\mu A$	--	780	--	$\mu A/V$
Oscillator Frequency	f_{SW}		--	1.2	--	MHz
Short Circuit Oscillation Frequency		$V_{FB} = 0V$	--	440	--	kHz
Maximum Duty Cycle	D_{MAX}	$V_{FB} = 0.8V$	--	80	--	%
Minimum On-Time	t_{ON}		--	100	--	ns
Under Voltage Lockout Threshold Rising			4	4.2	4.5	V
Under Voltage Lockout Threshold Hysteresis			--	300	--	mV
En input Low Voltage			--	--	0.4	V
En input High Voltage			1.4	--	--	V
Enable Pull Up Current			--	1	--	μA

To be continued

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Shutdown Current	I _{SHDN}	V _{EN} = 0V	--	25	50	μA
Quiescent Current	I _Q	V _{EN} = 2V, V _{FB} = 1.5V	--	0.7	1	mA
Thermal Shutdown	T _{SD}		--	150	--	°C

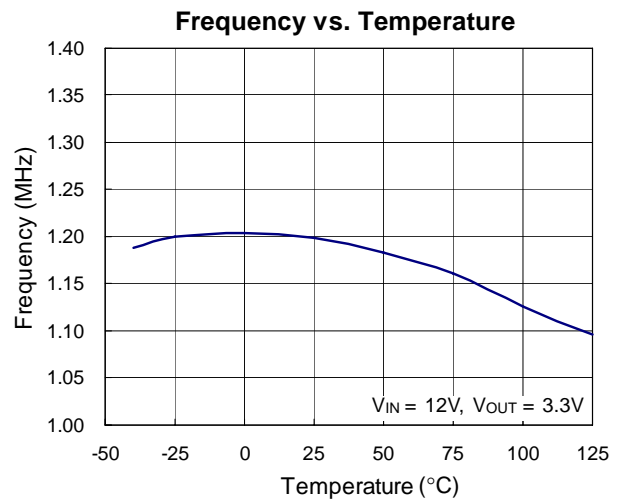
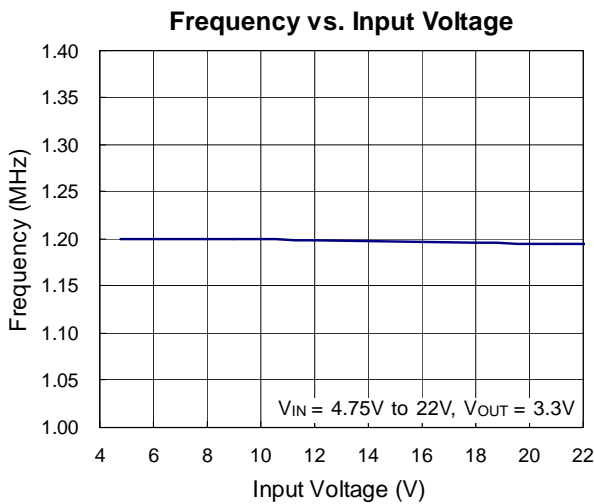
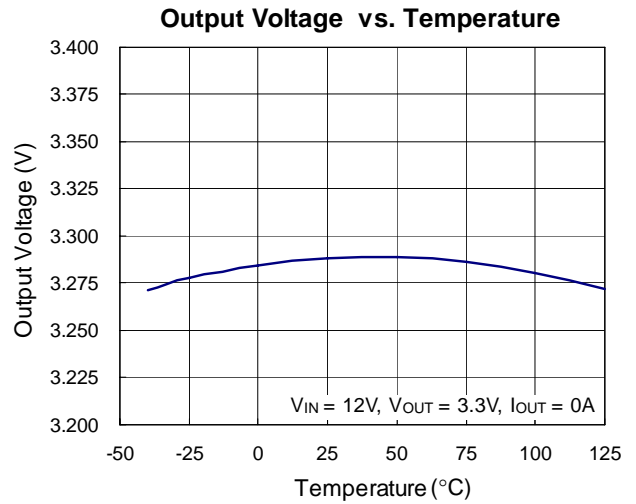
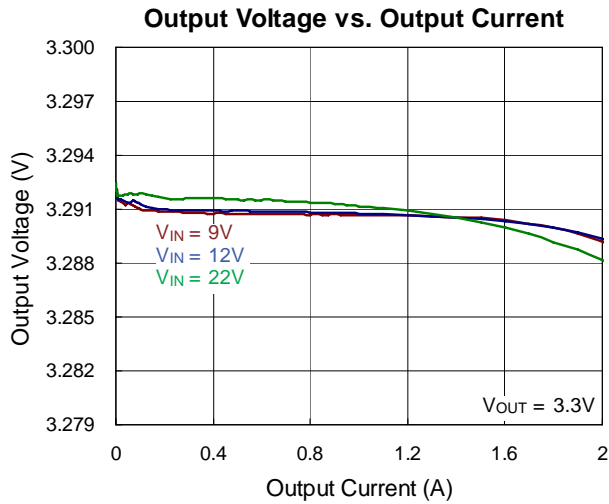
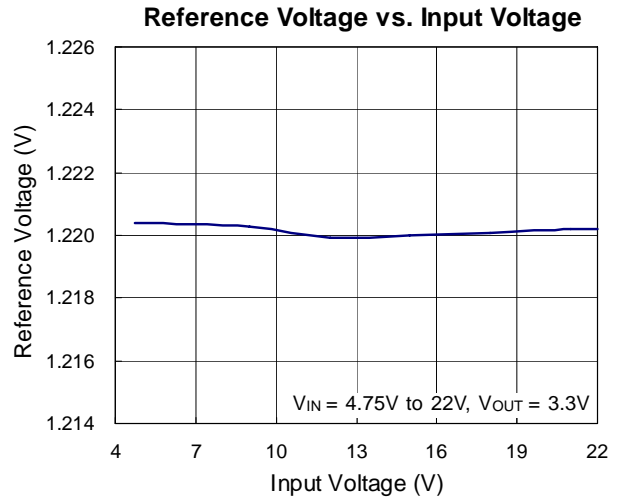
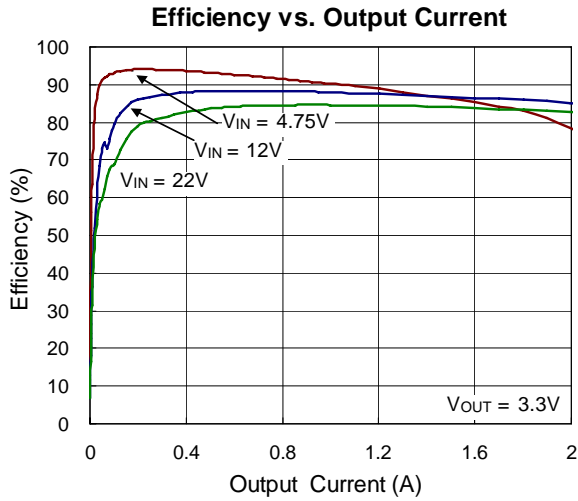
Note 1. Stresses listed as the above "Absolute Maximum Ratings" may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may remain possibility to affect device reliability.

Note 2. θ_{JA} is measured in the natural convection at T_A = 25°C on a high effective four layers thermal conductivity test board of JEDEC 51-7 thermal measurement standard.

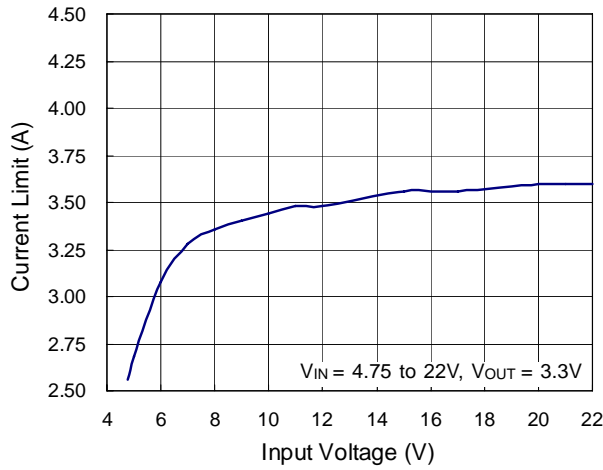
Note 3. Devices are ESD sensitive. Handling precaution is recommended.

Note 4. The device is not guaranteed to function outside its operating conditions.

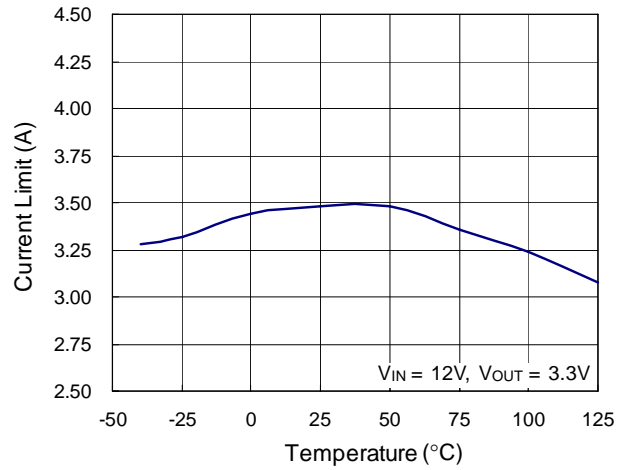
Typical Operating Characteristics



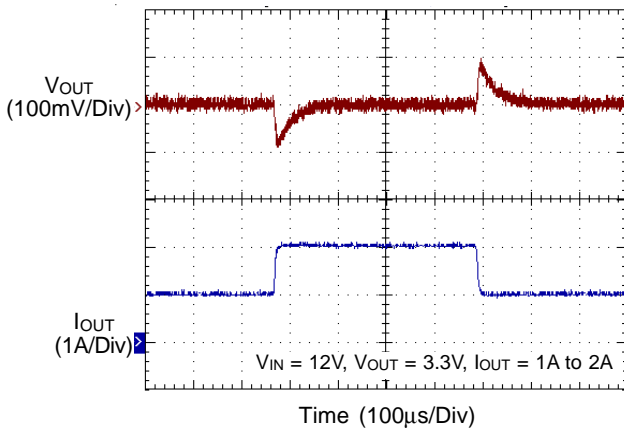
Current Limit vs. Input Voltage



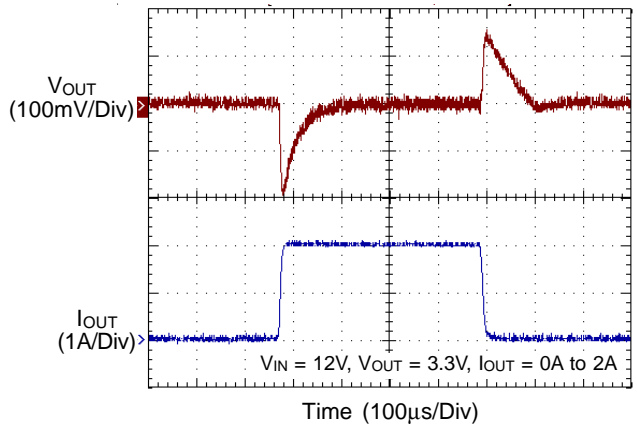
Current Limit vs. Temperature



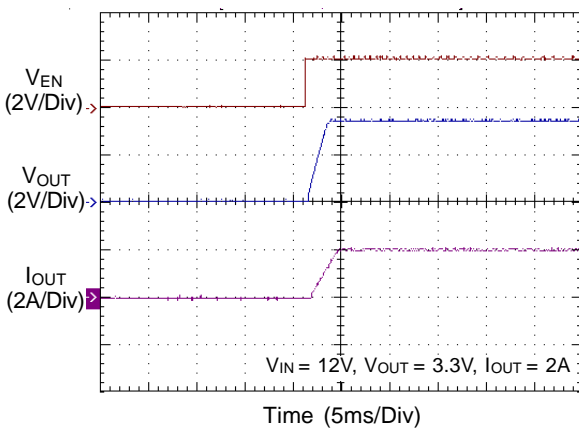
Load Transient Response



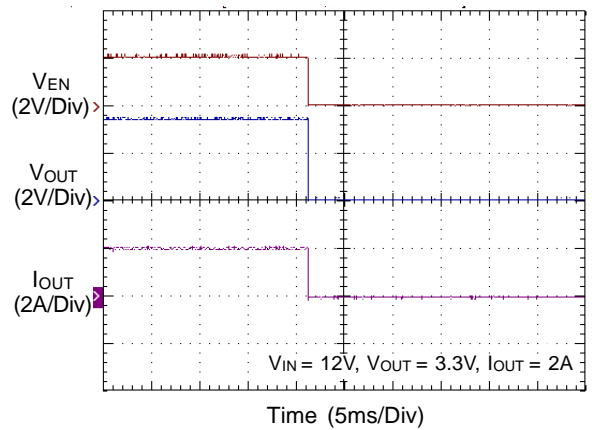
Load Transient Response

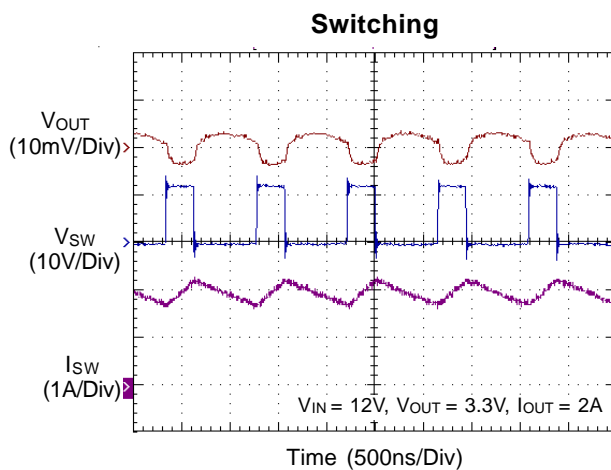
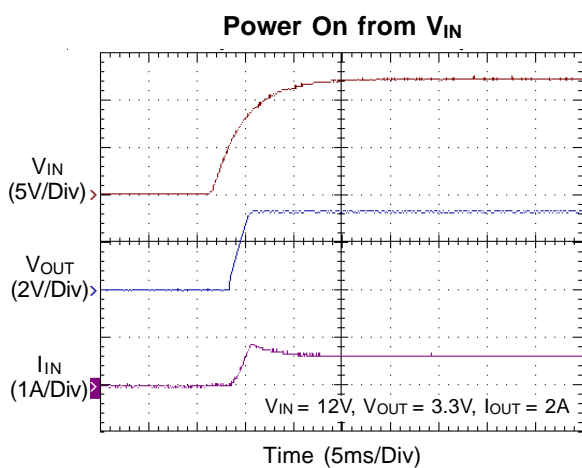


Power On from EN



Power Off from EN





Application Information

The RT8270 is an asynchronous high voltage buck converter that can support the input voltage range from 4.75V to 22V and the output current can be up to 2A.

Output Voltage Setting

The resistive divider allows the FB pin to sense the output voltage as shown in Figure 1.

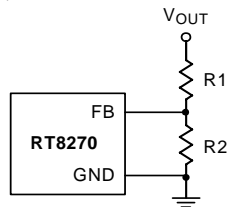


Figure 1. Output Voltage Setting

The output voltage is set by an external resistive divider according to the following equation :

$$V_{OUT} = V_{FB} \left(1 + \frac{R1}{R2} \right)$$

Where V_{FB} is the feedback reference voltage (1.222V typ.).

External Bootstrap Diode

Connect a 10nF low ESR ceramic capacitor between the BOOT pin and SW pin. This capacitor provides the gate driver voltage for the high side MOSFET.

It is recommended to add an external bootstrap diode between an external 5V and the BOOT pin for efficiency improvement when input voltage is lower than 5.5V or duty ratio is higher than 65%. The bootstrap diode can be a low cost one such as 1N4148 or BAT54.

The external 5V can be a 5V fixed input from system or a 5V output of the RT8270.

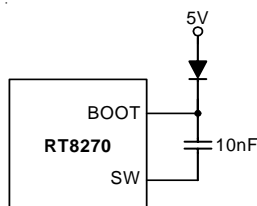


Figure 2

Soft-Start

The RT8270 contains an internal soft-start clamp that gradually raises the output voltage. The soft-start time is designed by the internal capacitor. The typical soft-start time is 2ms.

Inductor Selection

The inductor value and operating frequency determine the ripple current according to a specific input and output voltage. The ripple current ΔI_L increases with higher V_{IN} and decreases with higher inductance.

$$\Delta I_L = \left[\frac{V_{OUT}}{f \times L} \right] \times \left[1 - \frac{V_{OUT}}{V_{IN}} \right]$$

Having a lower ripple current reduces not only the ESR losses in the output capacitors but also the output voltage ripple. High frequency with small ripple current can achieve highest efficiency operation. However, it requires a large inductor to achieve this goal.

For the ripple current selection, the value of $\Delta I_L = 0.4(I_{MAX})$ will be a reasonable starting point. The largest ripple current occurs at the highest V_{IN} . To guarantee that the ripple current stays below the specified maximum, the inductor value should be chosen according to the following equation :

$$L = \left[\frac{V_{OUT}}{f \times \Delta I_L(MAX)} \right] \times \left[1 - \frac{V_{OUT}}{V_{IN(MAX)}} \right]$$

Inductor Core Selection

The inductor type must be selected once the value for L is known. Generally speaking, high efficiency converters can not afford the core loss found in low cost powdered iron cores. So, the more expensive ferrite or mollypermalloy cores will be a better choice.

The selected inductance rather than the core size for a fixed inductor value is the key for actual core loss. As the inductance increases, core losses decrease. Unfortunately, increase of the inductance requires more turns of wire and therefore the copper losses will increase.

Ferrite designs are preferred at high switching frequency due to the characteristics of very low core losses. So, design goals can focus on the reduction of copper loss and the saturation prevention.

Ferrite core material saturates “hard”, which means that inductance collapses abruptly when the peak design current is exceeded. The previous situation results in an abrupt increase in inductor ripple current and consequent output voltage ripple.

Do not allow the core to saturate!

Different core materials and shapes will change the size/ current and price/current relationship of an inductor.

Toroid or shielded pot cores in ferrite or permalloy materials are small and do not radiate energy. However, they are usually more expensive than the similar powdered iron inductors. The rule for inductor choice mainly depends on the price vs. size requirement and any radiated field/ EMI requirements.

Diode Selection

When the power switch turns off, the path for the current is through the diode connected between the switch output and ground. This forward biased diode must have a minimum voltage drop and recovery times. Schottky diode is recommended and it should be able to handle those current. The reverse voltage rating of the diode should be greater than the maximum input voltage, and current rating should be greater than the maximum load current. For more detail, please refer to Table 4.

C_{IN} and C_{OUT} Selection

The input capacitance, C_{IN}, is needed to filter the trapezoidal current at the source of the high side MOSFET. To prevent large ripple current, a low ESR input capacitor sized for the maximum RMS current should be used. The RMS current is given by :

$$I_{RMS} = I_{OUT(MAX)} \frac{V_{OUT}}{V_{IN}} \sqrt{\frac{V_{IN}}{V_{OUT}} - 1}$$

This formula has a maximum at V_{IN} = 2V_{OUT}, where I_{RMS} = I_{OUT}/2. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief.

Choose a capacitor rated at a higher temperature than required. Several capacitors may also be paralleled to meet size or height requirements in the design.

For the input capacitor, a 10μF low ESR ceramic capacitor is recommended. For the recommended capacitor, please

refer to table 3 for more detail.

The selection of C_{OUT} is determined by the required ESR to minimize voltage ripple.

Moreover, the amount of bulk capacitance is also a key for C_{OUT} selection to ensure that the control loop is stable. Loop stability can be checked by viewing the load transient response as described in a later section.

The output ripple, ΔV_{OUT}, is determined by :

$$\Delta V_{OUT} \leq \Delta I_L \left[ESR + \frac{1}{8fC_{OUT}} \right]$$

The output ripple will be highest at the maximum input voltage since ΔI_L increases with input voltage. Multiple capacitors placed in parallel may be needed to meet the ESR and RMS current handling requirement. Dry tantalum, special polymer, aluminum electrolytic and ceramic capacitors are all available in surface mount packages. Special polymer capacitors offer very low ESR value. However, it provides lower capacitance density than other types. Although Tantalum capacitors have the highest capacitance density, it is important to only use types that pass the surge test for use in switching power supplies. Aluminum electrolytic capacitors have significantly higher ESR. However, it can be used in cost-sensitive applications for ripple current rating and long term reliability considerations. Ceramic capacitors have excellent low ESR characteristics but can have a high voltage coefficient and audible piezoelectric effects. The high Q of ceramic capacitors with trace inductance can also lead to significant ringing.

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. However, care must be taken when these capacitors are used at input and output. When a ceramic capacitor is used at the input and the power is supplied by a wall adapter through long wires, a load step at the output can induce ringing at the input, V_{IN}. At best, this ringing can couple to the output and be mistaken as loop instability. At worst, a sudden inrush of current through the long wires can potentially cause a voltage spike at V_{IN} large enough to damage the part.

Checking Transient Response

The regulator loop response can be checked by looking at the load transient response. Switching regulators take several cycles to respond to a step in load current. When a load step occurs, V_{OUT} immediately shifts by an amount equal to ΔI_{LOAD} (ESR) and also begins to charge or discharge C_{OUT} generating a feedback error signal for the regulator to return V_{OUT} to its steady-state value. During this recovery time, V_{OUT} can be monitored for overshoot or ringing that would indicate a stability problem.

Thermal Considerations

The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surroundings airflow and temperature difference between junction to ambient. The maximum power dissipation can be calculated by following formula :

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

Where $T_{J(MAX)}$ is the maximum operation junction temperature, T_A is the ambient temperature and the θ_{JA} is the junction to ambient thermal resistance.

For recommended operating conditions specification of RT8270, the maximum junction temperature is 125°C. The junction to ambient thermal resistance θ_{JA} for SOP-8 package is 120°C/W on the standard JEDEC 51-7 four-layers thermal test board. The maximum power dissipation at $T_A = 25^\circ\text{C}$ can be calculated by following formula :

$$P_{D(MAX)} = (125^\circ\text{C} - 25^\circ\text{C}) / (120^\circ\text{C}/\text{W}) = 0.833\text{W for SOP-8 packages}$$

The maximum power dissipation depends on operating ambient temperature for fixed $T_{J(MAX)}$ and thermal resistance θ_{JA} . For RT8270 packages, the Figure 3 of derating curves allows the designer to see the effect of rising ambient temperature on the maximum power allowed.

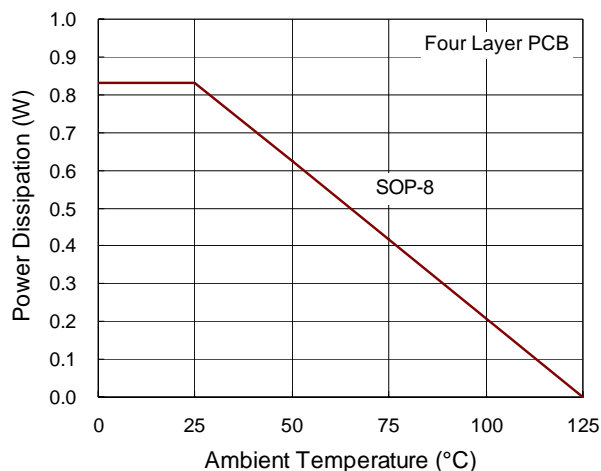


Figure 3. Derating Curves for RT8270 Packages

Layout Consideration

Follow the PCB layout guidelines for optimal performance of the RT8270.

- ▶ Keep the traces of the main current paths as short and wide as possible.
- ▶ Put the input capacitor as close as possible to the device pins (VIN and GND).
- ▶ LX node is with high frequency voltage swing and should be kept at small area. Keep sensitive components away from the LX node to prevent stray capacitive noise pick-up.
- ▶ Place the feedback components to the FB pin as close as possible.
- ▶ The GND and Exposed Pad should be connected to a strong ground plane for heat sinking and noise protection.

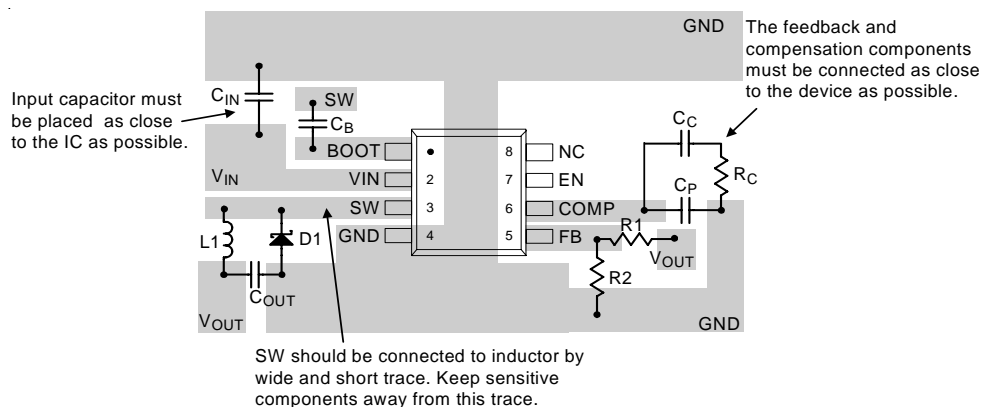


Figure 4. PCB Layout Guide

Table 2. Suggested Inductors for Typical Application Circuit

Component Supplier	Series	Dimensions (mm)
TDK	SLF12555T	12.5 x 12.5 x 5.5
TAIYO YUDEN	NR8040	8 x 8 x 4
TDK	SLF12565T	12.5 x 12.5 x 6.5

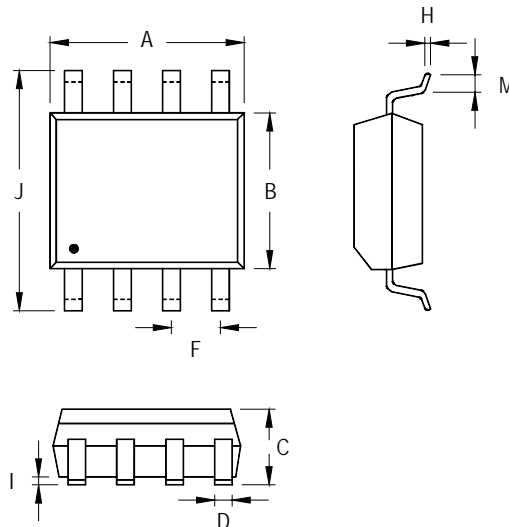
Table 3. Suggested Capacitors for C_{IN} and C_{OUT}

Location	Component Supplier	Part No.	Capacitance (μF)	Case Size
C _{IN}	MURATA	GRM31CR61E106K	10	1206
C _{IN}	TDK	C3225X5R1E106K	10	1206
C _{IN}	TAIYO YUDEN	TMK316BJ106ML	10	1206
C _{OUT}	MURATA	GRM32ER61E226M	22	1210
C _{OUT}	TDK	C3225X5R0J226M	22	1210
C _{OUT}	TAIYO YUDEN	EMK325BJ226MM	22	1210

Table 4. Suggested Diode

Component Supplier	Series	V _{RRM} (V)	I _{OUT} (A)	Package
DIODES	B330A	30	3	SMA
PANJIT	SK23	30	2	DO-214AA

Outline Dimension



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.801	5.004	0.189	0.197
B	3.810	3.988	0.150	0.157
C	1.346	1.753	0.053	0.069
D	0.330	0.508	0.013	0.020
F	1.194	1.346	0.047	0.053
H	0.170	0.254	0.007	0.010
I	0.050	0.254	0.002	0.010
J	5.791	6.200	0.228	0.244
M	0.400	1.270	0.016	0.050

8-Lead SOP Plastic Package

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